

# BRMJD31CDP

Rev.B .May.-2018

## / Descriptions

TO-252      NPN      Silicon NPN transistor in a TO-252 Plastic Package.

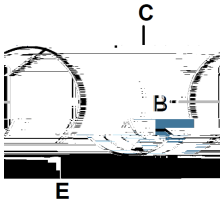
## / Features

$BV_{CEO} > 100V$ ;  
 $I_C = 3A$  high Continuous Collector Current;  
 $I_{CM} = 5A$  Peak Pulse Current;

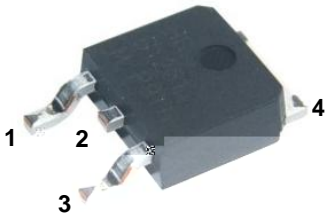
## / Applications

Power Switching or Amplification Applications

## / Equivalent Circuit



## / Pinning



PIN1 Base      PIN 2 4 Collector      PIN 3 Emitter

## / $h_{FE}$ Classifications & Marking

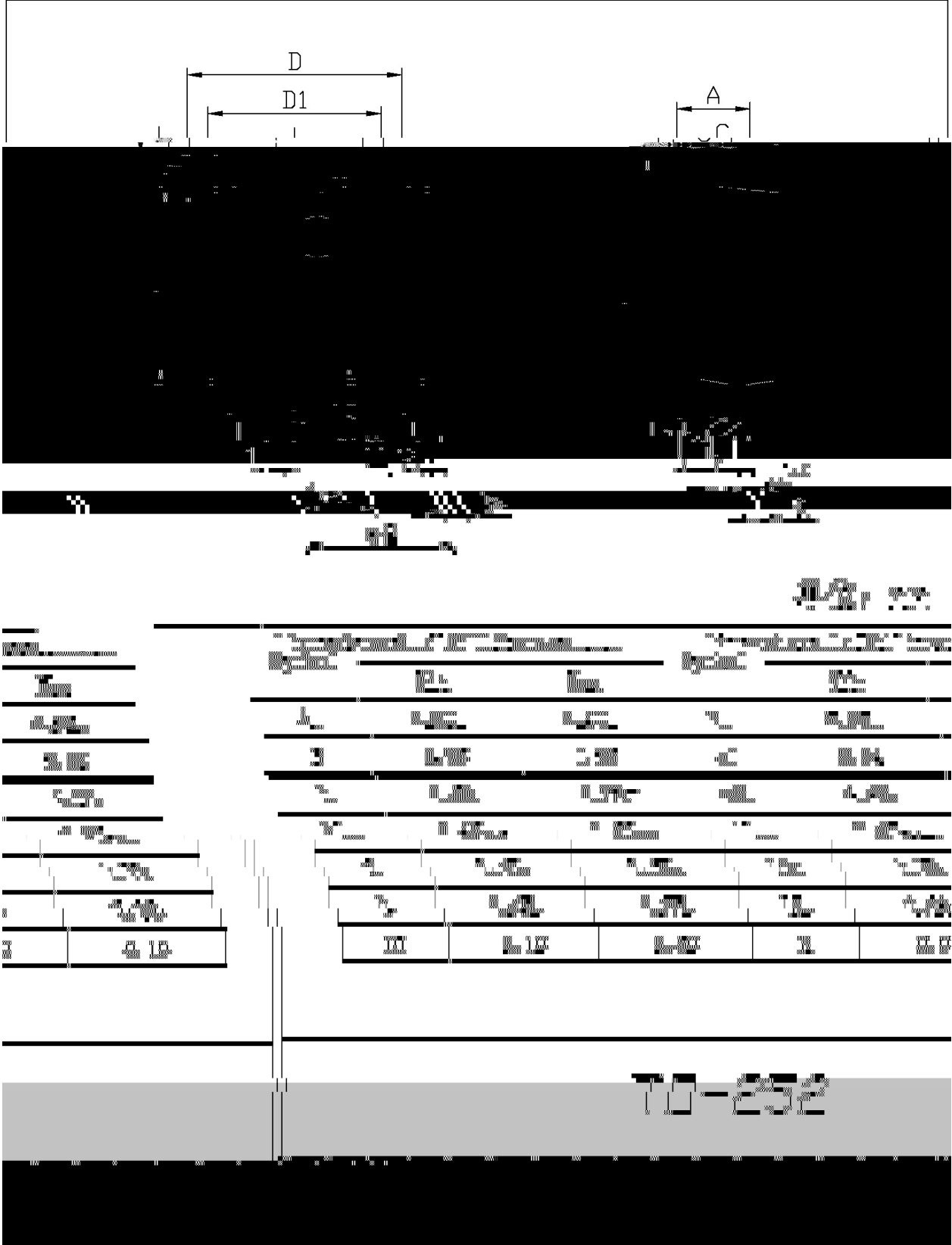
See Marking Instructions.

**BRMJD31CDP**

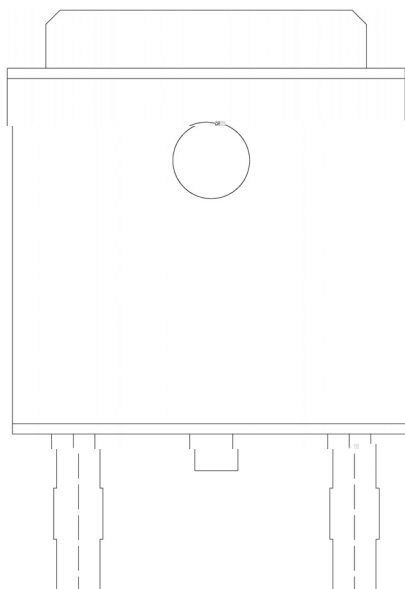


**BRMJD31CDP**

/ Package Dimensions



**/ Marking Instructions**



BR

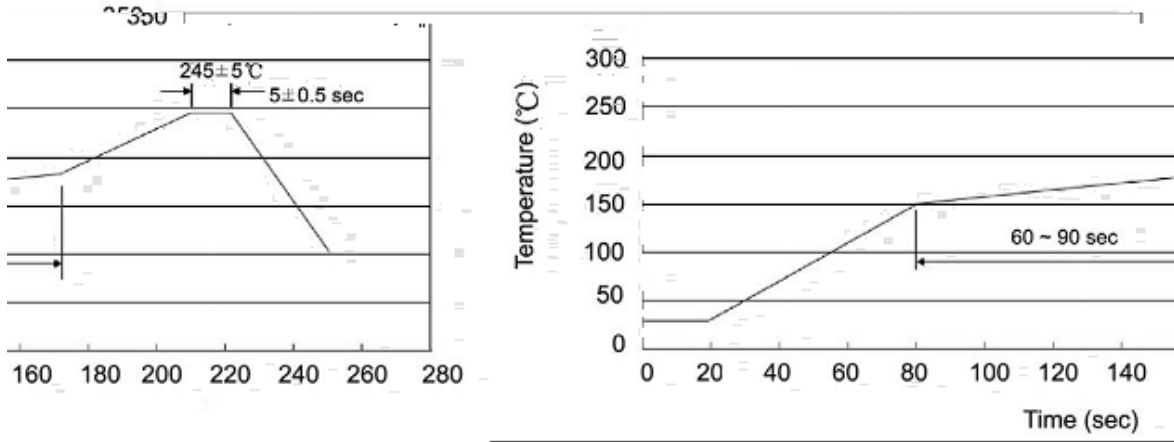
MJD31C

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Note:

BR:

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- |   |         |           |                                       |
|---|---------|-----------|---------------------------------------|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5   | 5±0.5sec; | 2.Peak Temp.:245±5                    |